

40N15

Power MOSFET

40A, 150V N-CHANNEL POWER MOSFET

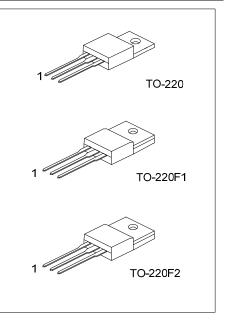
DESCRIPTION

The UTC **40N15** is a N-channel enhancement MOSFET, it uses UTC's advanced technology to provide the customers with perfect $R_{\text{DS}(\text{ON})}$, high switching speed, high current capacity and low gate charge.

FEATURES

- * $R_{DS(ON)}$ < 50m Ω @ V_{GS}=10V, I_D=20A
- * High Switching Speed
- * High Current Capacity

ORDERING INFORMATION

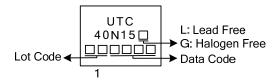


Ordering Number		Pin Assignment			Decking	
Halogen Free	Гаскауе	1	2	3	Packing	
40N15G-TA3-T	TO-220	G	D	S	Tube	
40N15G-TF1-T	TO-220F1	G	D	S	Tube	
40N15G-TF2-T	TO-220F2	G	D	S	Tube	
	Halogen Free 40N15G-TA3-T 40N15G-TF1-T	Halogen FreePackage40N15G-TA3-TTO-22040N15G-TF1-TTO-220F1	Halogen FreePackage40N15G-TA3-TTO-22040N15G-TF1-TTO-220F1G	Halogen FreePackage40N15G-TA3-TTO-220G40N15G-TF1-TTO-220F1GD	Halogen Free Package 1 2 3 40N15G-TA3-T TO-220 G D S 40N15G-TF1-T TO-220F1 G D S	

Note: Pin Assignment: G: Gate D: Drain S: Source

(1) T: Tube			
(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2			
(3) G: Halogen Free and Lead Free, L: Lead Free			
(,			

MARKING



ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	150	V
Gate-Source Voltage		V _{GSS}	±25	V
Drain Current	Continuous	ID	40	А
	Pulsed	I _{DM}	180	А
Avalanche Current		I _{AR}	45.6	А
Avalanche Energy	Single Pulsed	E _{AS}	650	mJ
	Repetitive	E _{AR}	21	mJ
Peak Diode Recovery dv/dt		dv/dt	7	V/ns
Power Dissipation	TO-220	Б	166	W
	TO-220F1/TO-220F2	PD	40	W
Junction Temperature		TJ	-50 ~ +150	°C
Storage Temperature Range		T _{STG}	-50 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL CHARACTERISTICS

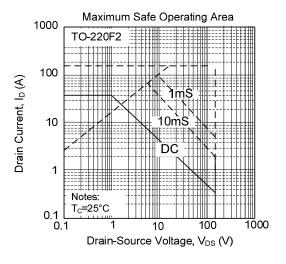
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ _{JA}	62.5	°C/W
Junction to Case	TO-220	0	0.9	°C/W
	TO-220F1/TO-220F2	θις	3.125	°C/W

■ ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250µA	150			V
Drain-Source Leakage Current		I _{DSS}	V _{GS} =0V, V _{DS} =150V			900	nA
Gate-Source Leakage Current	Forward	– I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS			-	_			
Gate Threshold Voltage	Gate Threshold Voltage		$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.2		3.8	V
Static Drain-Source On-State Resi	Static Drain-Source On-State Resistance		V _{GS} =10V, I _D =20A			50	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}			2500		pF
Output Capacitance		C _{oss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		520		pF
Reverse Transfer Capacitance	Reverse Transfer Capacitance		1-1.0MHZ		100		рF
SWITCHING PARAMETERS		C _{RSS}					
Total Gate Charge		Q_{G}			85		nC
Gate to Source Charge		Q_{GS}	V _{GS} =10V, V _{DD} =50V, I _D =1.3A, I _G =100µA		15		nC
Gate to Drain Charge		Q_{GD}	$I_{\rm D}$ = 1.3A, $I_{\rm G}$ = 100 μ A		41		nC
Turn-ON Delay Time		t _{D(ON)}			35		ns
Rise Time		t _R	V _{GS} =0~10V, V _{DD} =30V,		320		ns
Turn-OFF Delay Time		t _{D(OFF)}	I _D =0.5A, R _G =25Ω		210		ns
Fall-Time		t _F			200		ns
SOURCE- DRAIN DIODE RATING	GS AND CI	HARACTERIS	TICS	-			
Maximum Body-Diode Continuous	Current	Is	SR CO			40	Α
Maximum Body-Diode Pulsed Curr	Maximum Body-Diode Pulsed Current		1 10 .08.			160	Α
Drain-Source Diode Forward Voltage		V _{SD}	I _S =40A, V _{GS} =0V			1.48	V
Body Diode Reverse Recovery Time		t _{RR}	V _{GS} =0V, I _S =30A		150		ns
Body Diode Reverse Recovery Charge		Q _{RR}	dl _⊧ /d _t =100A/µs		0.9		μC
	_	Q _{RR} J.M.	N				



TYPICAL CHARACTERISTICS



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